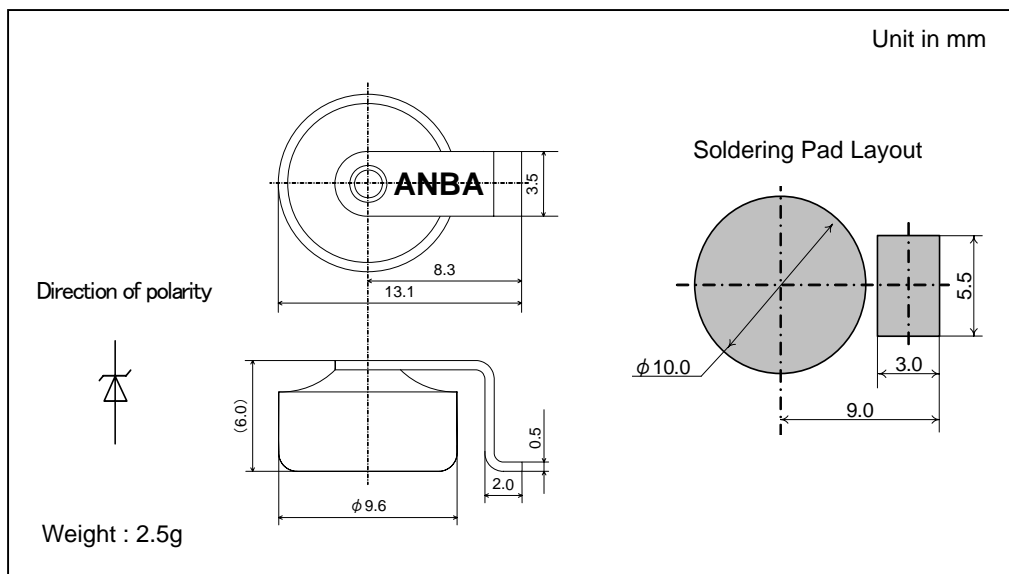


ZSH8MD27

FEATURES

- High transient reverse power capability suitable for Load Dump Surge protecting for automobile electronic components etc.
- ISO7637-2 Pulse 5a Ri=0.5 ohm capable.

OUTLINE DRAWING

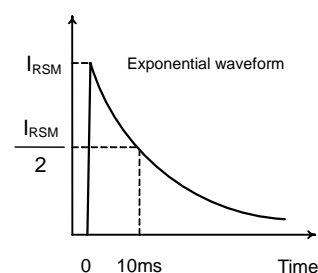


ABSOLUTE MAXIMUM RATINGS

Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	P_{RSM}	W	5,700(Rectangular pulse $t=1ms$ $T_j=25^\circ C$ start)
Non-Repetitive Peak Reverse Surge Current	I_{RSM}	A	130(Exponential waveform. See Fig.1, $T_j=25^\circ C$ start)
DC Reverse Voltage	V_{DC}	V	22
Operating Junction Temperature	T_j	$^\circ C$	-40 ~ +150
Storage Temperature	T_{stg}	$^\circ C$	-40 ~ +150

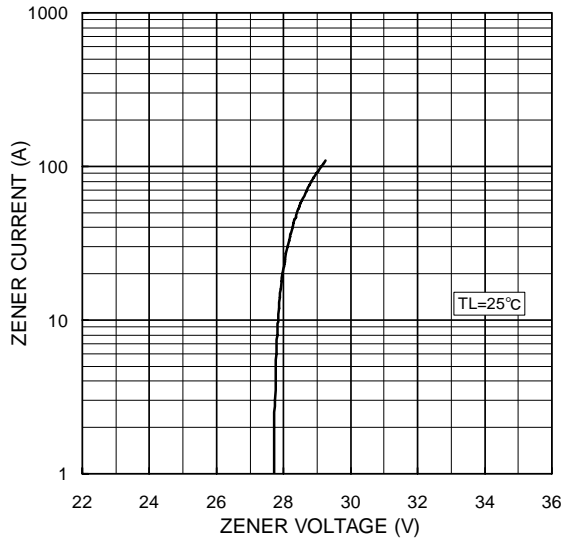
CHARACTERISTICS($T_L=25^\circ C$)

Items	Symbols	Units	Min.	Typ.	Max.	Test Conditions
Zener Voltage	V_Z	V	24.0	27.0	30.0	$I_Z=10mA$
Dynamic Impedance	Z_Z	Ω	-	-	50	$I_Z=10mA$
Zener Voltage Temperature Coefficient	γ_Z	$\%/^\circ C$	-	0.081	-	$I_Z=10mA$
Peak Forward Voltage	V_{FM}	V	-	-	0.98	$I_{FM}=6A$
Peak Reverse Current	I_{RRM}	μA	-	-	10	$V_R=22V$

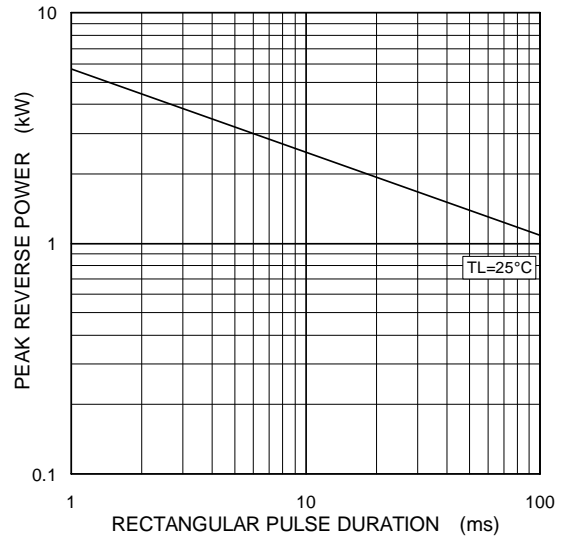
Figure 1. I_{RSM} waveform

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Typical zener characteristics



Typical reverse power characteristics
(Rectangular pulse non-repetitive)



HITACHI POWER SEMICONDUCTORS

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